

# 2SA2140

## Silicon PNP epitaxial planar type

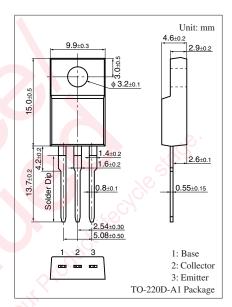
For power amplification For TV VM circuit

#### ■ Features

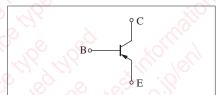
- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- High transition frequency (f<sub>T</sub>)
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	-180	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-180	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-6	V	
Collector current	$I_{C}$	-1.5	A	
Peak collector current	$I_{CP}$	-3	A	
Collector power dissipation	P <sub>C</sub>	20	W	
$T_a = 25^{\circ}C$		2.0	1,0	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	o CXC	



#### Internal Connection



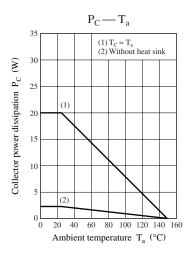
### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

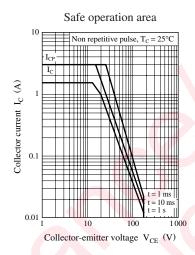
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -10 \text{ mA}, I_B = 0$	-180			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -180 \text{ V}, I_E = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -6 \text{ V}, I_C = 0$			-100	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = -5 \text{ V}, I_{C} = -0.1 \text{ A}$	60		240	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -1 A, I_B = -0.1 A$			- 0.5	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -0.2 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		30		pF
(Common base, input open circuited)		So Ville				
Turn-on time	t <sub>on</sub>	$I_C = -0.4$ A, Resistance loaded		0.1		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.04 \text{ A}, I_{B2} = -0.04 \text{ A}$		1.0		μs
Fall time	t <sub>f</sub>	$V_{CC} = 100 \text{ V}$		0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

Rank	Q	Р
$h_{FE}$	60 to 140	120 to 240





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